
2SA1468

Silicon PNP Epitaxial

HITACHI

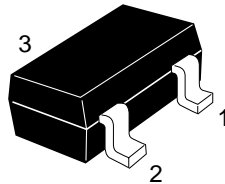
ADE-208-1018 (Z)
1st. Edition
Mar. 2001

Application

High voltage amplifier

Outline

MPAK



1. Emitter
2. Base
3. Collector

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-180	V
Collector to emitter voltage	V_{CEO}	-180	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

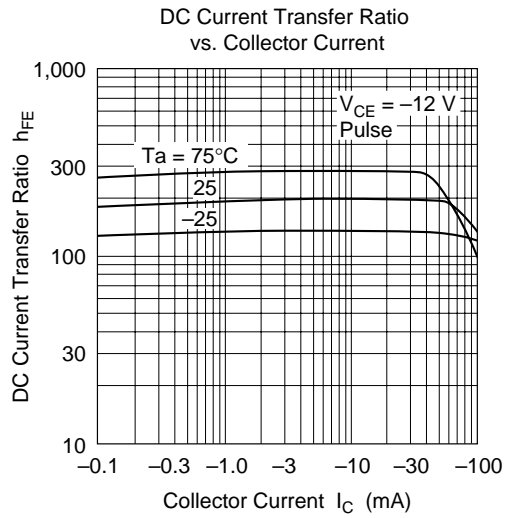
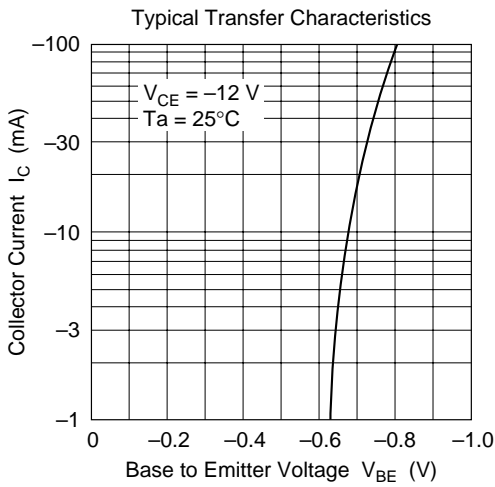
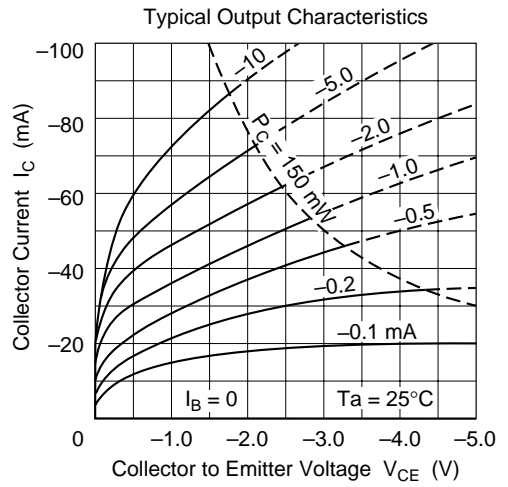
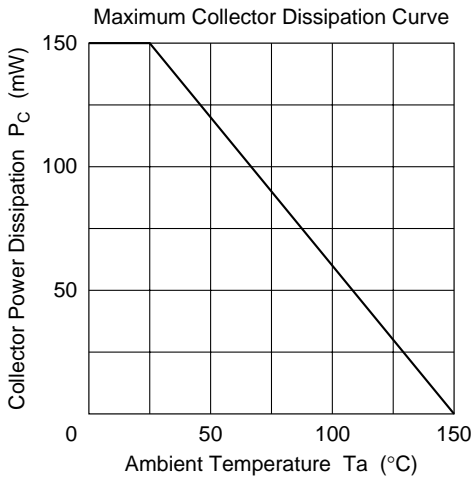
Electrical Characteristics (Ta = 25°C)

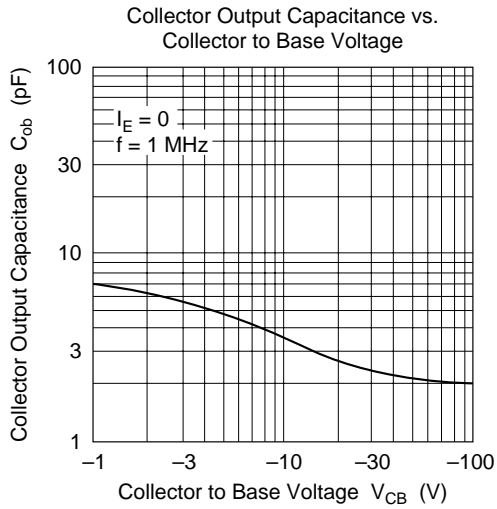
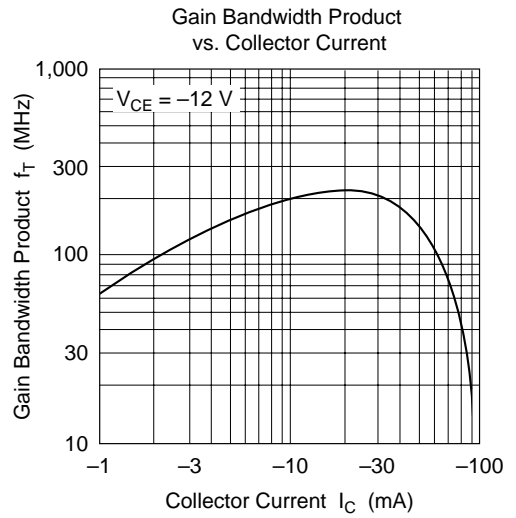
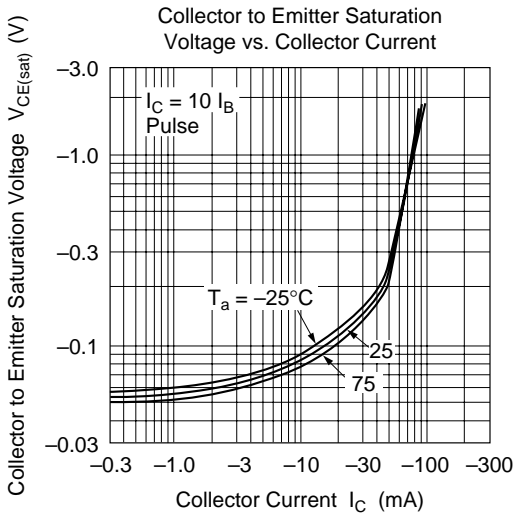
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-180	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-180	—	—	V	$I_C = -0.5 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	320		$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.5	V	$I_C = -30 \text{ mA}, I_B = -3 \text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	—	—	-1.0	V	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Gain bandwidth product	f_T	—	200	—	MHz	$V_{CE} = -12 \text{ V}, I_C = -10 \text{ mA}$
Collector output capacitance	C_{ob}	—	3.5	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Notes: 1. The 2SA1468 is grouped by h_{FE} as follows.

2. Pulse test

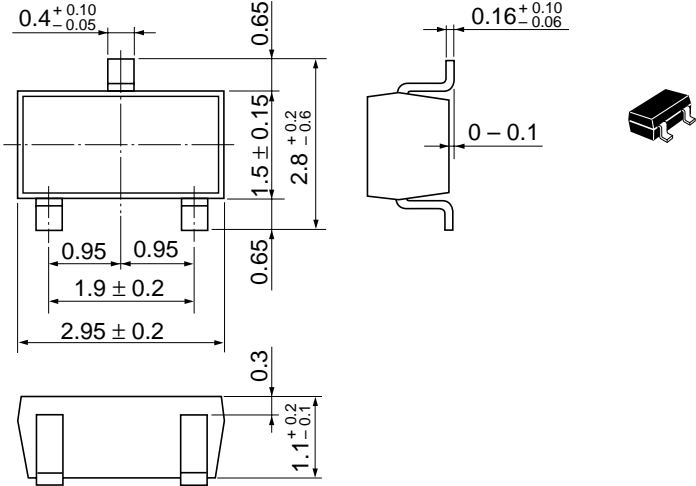
Grade	B	C
Mark	INB	INC
h_{FE}	100 to 200	160 to 320





Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.011 g

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